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An Electrophysiological Model of Working Memory Performance

Golnaz Baghdadi, Farzad Towhidkhah, Reza Rostami

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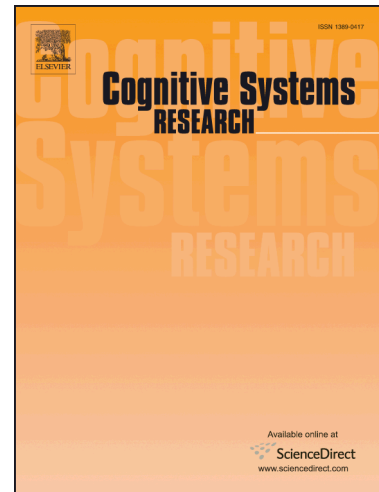
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Golnaz Baghdadi¹, Farzad Towhidkhan^{1*}, Reza Rostami²

¹ Department of Biomedical Engineering, Amirkabir University of Technology, Tehran, Iran

² Department of Psychology and Educational Sciences, University of Tehran, Tehran, Iran

***Corresponding Author:** Farzad Towhidkhan

Address: Biomedical Engineering Department, Amirkabir University of Technology, 424

Hafez Ave, Tehran, I.R. Iran, 15875-4413.

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